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Prof. Gong Xiao

(National University of Singapore, Singapore)



Dr. Gong Xiao is currently an Associate Professor in the ECE Department of the National University of Singapore (NUS). He obtained his Ph. D Degree from NUS and was a Visiting Scientist at MIT in the year of 2014. His research interest includes advanced transistors and emerging memories for in-memory computing, monolithic 3D integration, opto-electronic integrated circuits and their applications in quantum technology, as well as ultra-high frequency and ultra-wide bandgap device technology. He has won many awards, including the Bronze Medal at the 6th TSMC Outstanding Student Researcher Award, the Best Student Paper Award at VLSI Symposium (2017 and 2021), the Best Demo Paper Award at VLSI Symposium (2022 and 2023), the Best Student Paper Award at ICICDT (2019, 2021, and 2023), Emerging Leaders in Journal of Physics D 2021, and NUS Engineering Teaching Excellence Award. He has more than 300 publications in international journals and conferences, including more than 70 papers in IEDM and VLSI Symposium. He is the Technical Program Chair in ICICDT (2019, 2022, 2023, 2024) and Sub-committee Chair in ICICDT (2021) and EDTM (2022, 2023, 2025), and in the technical committees of IEDM (2021, 2022), VLSI-TSA (2022, 2023, 2024), ECS (2014, 2016, 2018, 2020, 2022, and 2024), ICMAT (2017), EDTM (2017 to 2021), IWJT (2021, 2023), etc. He is the Editor of IEEE Electron Device Letters.